

20N15-HC

Power MOSFET

20A, 150V N-CHANNEL POWER MOSFET

■ DESCRIPTION

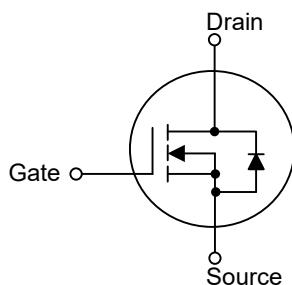
The UTC **20N15-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **20N15-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

■ FEATURES

- * $R_{DS(ON)} \leq 0.105 \Omega$ @ $V_{GS}=10V$, $I_D=10A$
- * High Switching Speed

■ SYMBOL



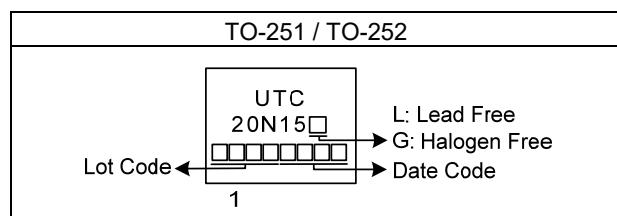
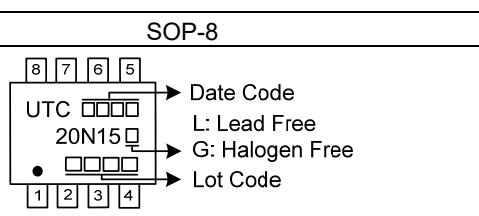
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
20N15L-TM3-T	20N15G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
20N15L-TN3-R	20N15G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
20N15L-S08-R	20N15G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

 20N15G-TM3-T (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TM3: TO-251, TN3: TO-252, S08: SOP-8 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

TO-251 / TO-252	SOP-8
 <p>UTC 20N15</p> <p>Lot Code ← Date Code → Date Code</p> <p>1</p>	 <p>UTC 20N15</p> <p>8 7 6 5 → Date Code L: Lead Free G: Halogen Free</p> <p>• 1 2 3 4 → Lot Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	Continuous	I_D	20	A
	Pulsed	I_{DM}	40	A
Single Pulsed Avalanche Current		I_{AS}	6	A
Single Pulsed Avalanche Energy		E_{AS}	541.8	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.7	V/ns
Power Dissipation	TO-251	P_D	46	W
	TO-252		5.5	W
	SOP-8			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. L=30mH, $I_{AS}=6.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 20\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient (Note)	TO-251	θ_{JA}	50	$^\circ\text{C/W}$
	TO-252		90	$^\circ\text{C/W}$
	SOP-8			
Junction to Case (Note)	TO-251	θ_{JC}	2.7	$^\circ\text{C/W}$
	TO-252		22.7	$^\circ\text{C/W}$
	SOP-8			

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

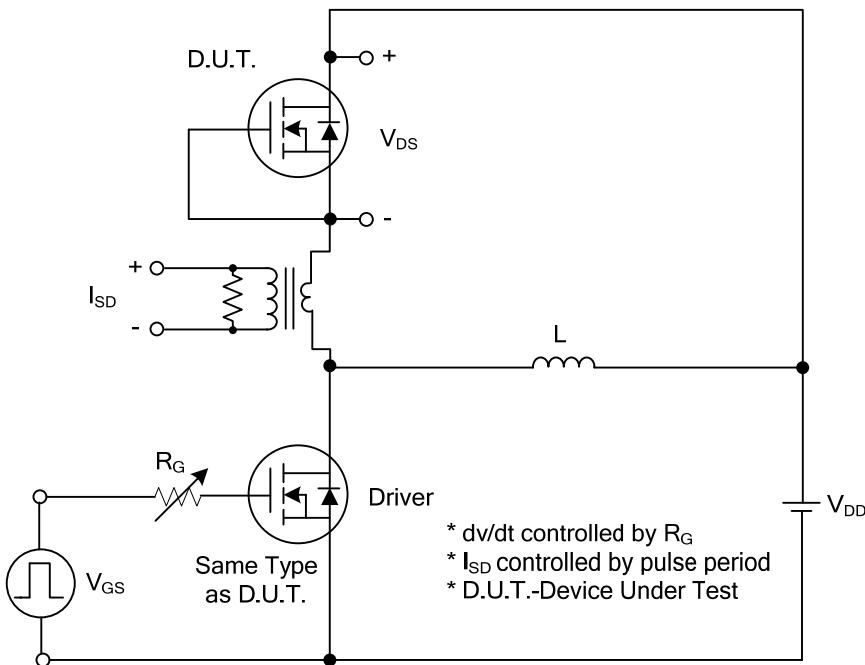
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	150			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=150\text{V}, V_{GS}=0\text{V}$		10		μA
Gate-Source Leakage Current	Forward	$V_{GS}=+20\text{V}, V_{DS}=0\text{V}$			+100	nA
	Reverse	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=10\text{A}$			0.105	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1.0\text{MHz}$		864.7		pF
Output Capacitance	C_{OSS}			185.6		pF
Reverse Transfer Capacitance	C_{RSS}			13.4		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=120\text{V}, V_{GS}=10\text{V}, I_D=20\text{A}$ $I_G=1\text{mA}$ (Note 1, 2)		21.6		nC
Gate to Source Charge	Q_{GS}			8.2		nC
Gate to Drain Charge	Q_{GD}			4.1		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{DD}=100\text{V}, V_{GS}=10\text{V}, I_D=20\text{A},$ $R_G=25\Omega$ (Note 1, 2)		7.8		ns
Rise Time	t_R			17.4		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			18		ns
Fall-Time	t_F			17.5		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				20	A
Maximum Body-Diode Pulsed Current	I_{SM}				40	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=20\text{A}, V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=20\text{A}, V_{GS}=0\text{V}, dI_F/dt=100\text{A}/\mu\text{s}$		95		ns
Reverse Recovery Charge	Q_{rr}	(Note 1)		0.6		μC

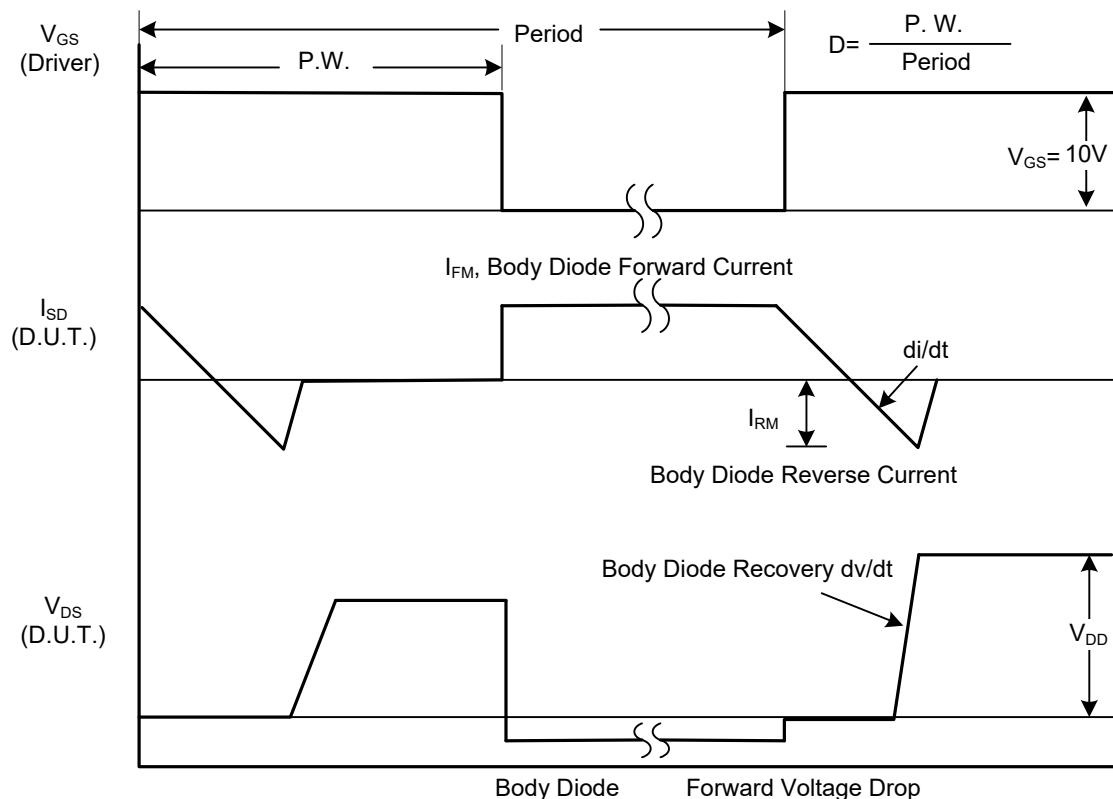
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

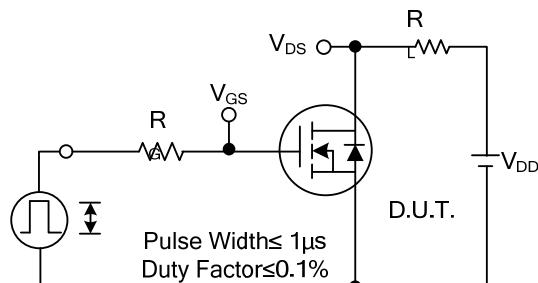


Peak Diode Recovery dv/dt Test Circuit

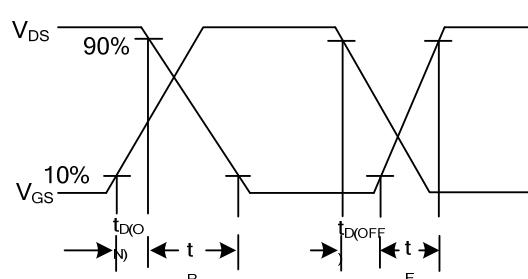


Peak Diode Recovery dv/dt Waveforms

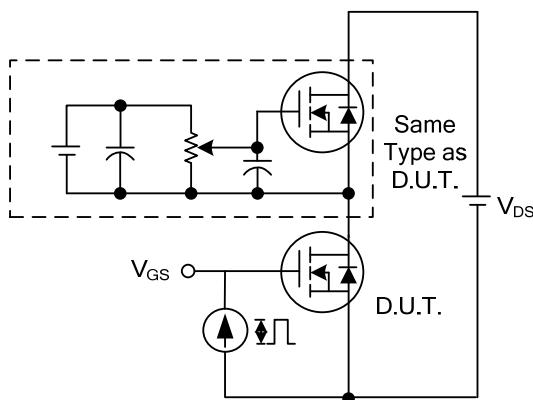
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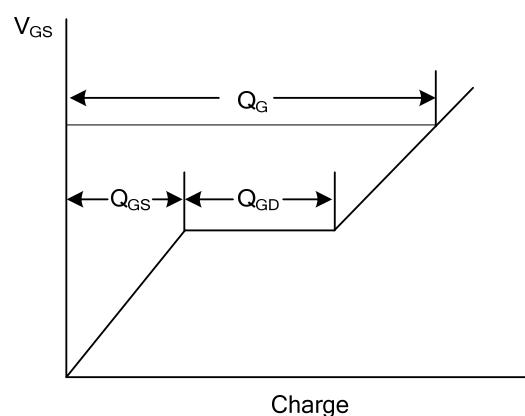
Switching Test Circuit



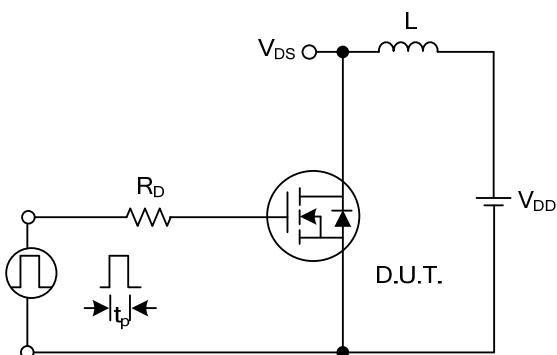
Switching Waveforms



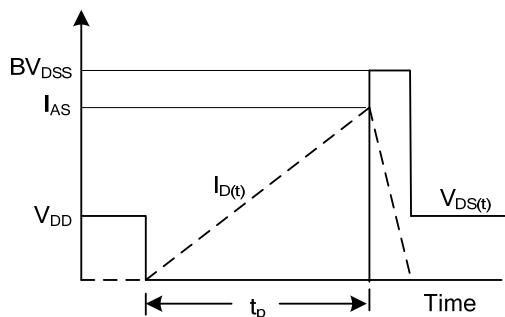
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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